

Wafer Fabs

by Dr Jeff Drobman Dr Jeff Software & CSUN

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ISA/SoC Landscape







Electronics Industry: US/UK/E



Electronics Industry: ROW



Chips Sales





Chips Sales



2Q21 Top 10 Semiconductor Sales Leaders (\$M, Including Foundries)

2Q21 Rank	1Q21 Rank	Company	Headquarters	1Q21 Total IC	1Q21 Total O-S-D	1Q21 Total Semi	2Q21 Total IC	2Q21 Total O-S-D	2Q21 Total Semi	2Q21/1Q21 % Change
1	2	Samsung	South Korea	16,152	920	17,072	19,262	1,035	20,297	19%
2	1	Intel	U.S.	18,676	0	18,676	19,304	0	19,304	3%
3	3	TSMC (1)	Taiwan	12,911	0	12,911	13,315	0	13,315	3%
4	4	SK Hynix	South Korea	7,270	358	7,628	8,762	451	9,213	21%
5	5	Micron	U.S.	6,629	0	6,629	7,681	0	7,681	16%
6	6	Qualcomm (2)	U.S.	6,281	0	6,281	6,472	0	6,472	3%
7	8	Nvidia (2)	U.S.	4,842	0	4,842	5,540	0	5,540	14%
8	7	Broadcom Inc. (2)	U.S.	4,364	485	4,849	4,400	490	4,890	1%
9	10	MediaTek (2)	Taiwan	3,849	0	3,849	4,496	0	4,496	17%
10	9	TI	U.S.	3,793	235	4,028	4,030	269	4,299	7%
— — Top-10 Total			84,767	1,998	86,765	93,262	2,245	95,507	10%	

(1) Foundry (2) Fabless

Source: Company reports, IC Insights' Strategic Reviews database

Top 10 IC Companies



Table 1: Global Top Ten IC Design Company Revenue Ranking, 1Q22 (Unit: US\$1 Millio							
1Q22 Rank	1Q21 Rank	Company	1Q22 Revenue	1Q21 Revenue	YoY		
1	1	Qualcomm	9,548	6,281	52%		
2	2	NVIDIA	7,904	5,173	53%		
3	3	Broadcom 6,110 4,849		26%			
4	5	AMD	5,887	3,445	71%		
5	4	MediaTek	5,007	3,805	32%		
6	9	Marvell T	1,412	821	72%		
7	6	Novatek	1,281	929	38%		
8	8	Realtek	1,044	822	27%		
9	-	Will Semiconductor	744	815	-9%		
10	-	Cirrus Logic	490	294	67%		
	7	Xilinx	-	851	-		
-	10 Dialog		-	366	-		
	27,342	44%					

Notes

1. This top ten ranking only accounts for companies ahead of public financial reporting.

2.Qualcomm revenue only includes QCT; NVDIA excludes OEM/IP revenue; Broadcom revenue only includes semiconductors; Will Semiconductor revenue only includes semiconductor design and sales.

3. NT\$:US\$ exchange rate: 1Q22 - 28.50:1; 1Q21 - 28.39:1

4. RMB:US\$ exchange rate: 1Q22 - 6.336:1; 1Q21 - 6.483:1

Source: TrendForce, Jun. 2022

Top 10 IC Companies



Leading MPU Suppliers (\$B)

2021 Rank	Company	Headquarters	2020	2021	21/20 % Chg	2021 % Marketshare
1	Intel	U.S.	50.6	52.3	3%	50.9%
2	Apple*	U.S.	10.5	13.4	27%	13.0%
3	Qualcomm	U.S.	7.4	9.4	26%	9.1%
4	AMD	U.S.	5.9	9.2	56%	8.9%
5	MediaTek	Taiwan	2.7	4.1	51%	4.0%

*Custom designs for Apple's products that are made by IC foundries. Source: Company reports, IC Insights

Chips Sales





WW Chip Sales



SIA A SEMICONDUCTOR INDUSTRY ASSOCIATION

Worldwide Semiconductor Revenues

Year-to-Year Percent Change



US Chip Industry



S I A SEMICONDUCTOR

The U.S. semiconductor industry is the worldwide leader with nearly half of global market share.

1,250,000+

The industry directly employs nearly 250,000 people in the U.S. and supports more than 1 million additional U.S. jobs.

WW Chip Shares







Source: Company financials, SIA analysis, WSTS, Omida

WW Sales by Segment by Are

S I A SEMICONDUCTOR INDUSTRY ASSOCIATION

Global Semiconductor Sales by Geographic Area, 2019 (%)



Source: UN Comtrade; BCG x SIA: Strengthening the Global Semiconductor Supply Chain in an Uncertain Era



SIA Members





IC Technology







CPU Trends





Original data up to the year 2010 collected and plotted by M. Horowitz, F. Labonte, O. Shacham, K. Olukotun, L. Hammond, and C. Batten New plot and data collected for 2010-2019 by K. Rupp

Timeline of CPU Speed





image: CPU Architecture War : Clock Speed v.s. Instruction-Level Parallelism [https://www.linkedin.com/pulse/cpu-architecture-war-clock-speed-vs-instruction-levelhanindhito]

CPU Trends





lain McClatchie

design verification on MIPS R8000, helped architect Beast · September 2

In the mid-2000s a bunch of effects simultaneously ended the party.

- Transconductance stopped getting better. Yes, there were still a couple of great tricks that got introduced after that (strained silicon and FinFETs), but the regular improvements ended.
- The delay from transistors finally scaled below the delay from wires, and wires had never been getting better.
- The number of logic stages per clock cycle dropped to about 20 inverter-load-4 delays, and it turns out that getting less than that makes your logic get impractically power hungry really quickly.
- It turned out that people just didn't want CPUs that used more than 100 watts. The business folks realized they were spending more money on the electricity to run the CPU than on the CPU.

Custom SoC's



Are tech giants, like Tesla, rushing to develop their own semiconductor chips because they do not like having to do things with their hands tied?



Jeff Drobman, Lecturer at California State University, Northridge (2016present)

Answered just now

Almost all, except Google, license existing CPU and GPU core designs from ARM which are manufactured by TSMC according to their own custom multi-core designs. Apple's SoC's are also based on ARM cores, but were customized by Apple in concert with ARM. Google alone designed their own CPU architecture called Tensor Processing Units.

Apple Event



















Gordon Moore

Jan 3, 1929 -- March 24, 2023

≪News+

Los Angeles Times Gordon E. Moore, Intel founder and creator of Moore's Law, dies at 94







Gordon Moore



Moore in 1978

Born	Gordon Earle Moore January 3, 1929 Pescadero, California, U.S. ^[1]
Died	March 24, 2023 (aged 94) Waimea, Hawaii, U.S.
Education	University of California, Berkeley (BS) California Institute of Technology (PhD)



transistorsdoublesevery 2 years



Plaque to Moore\'s Law at the technology plaza in Mountain View, beneath a model of the Silicon crystal

Dave Laws (2018)

Number of transistors

Chips-Moore's Law









Looking Back

- Original in 1965: # Transistors will double every year (12 months)
- Moore revised his prediction in 1975: double every 2 years (24 months)
 - → THIS IS MOORE'S LAW
- Intel's exec David House added CPU complexity would double every 18 months
- History shows # Transistors has doubled every
 - 2 years in *logic*18 months in DRAM/SRAM





Origin of Moore's Law





DR JEFF

SOF

Jeff Drobman ©2016-23

DS.

Dr Jeff

Figure 3. Gordon Moore notes on IC device types. Collection of the Computer History Museum, 102783359.

Year	Device	Function	Transistors	Resistors	Components	LOG ₂
1959	2N697	Transistor	1	0	1	0
1962	Type G	RTL 3 - I/P gate	3	4	7	2.8
1963 (late 62)	Type R	RTL D Flip Flop	15	18	33	5.0
1964	945	DTL R-S Flip Flop	13	21	34	5.1
1965 (late 64)	958	RTL Counter	33	25	58	5.9
1966	9300	TTL Shift Register	85	40	125	7.0
1967	4500	DTL 32- Gate Array	200	64	264*	8.0

Figure 4. Table of component count for devices in photograph.

Microprocessor Timeline



Moore's Law – The number of transistors on integrated circuit chips (1971-2016) Our World

Moore's law describes the empirical regularity that the number of transistors on integrated circuits doubles approximately every two years. This advancement is important as other aspects of technological progress – such as processing speed or the price of electronic products – are strongly linked to Moore's law.



Data source: Wikipedia (https://en.wikipedia.org/wiki/Transistor_count)

The data visualization is available at OurWorldinData.org. There you find more visualizations and research on this topic.

Memory Timeline





Hard disk storage has become denser at an exponential rate over the last 50 years, just like main memory. The dramatic increase in capacity and speed of both has fueled the increasing power of computers.

Moore's Scale





and comparison of sizes of semiconductor manufacturing process nodes with some microscopic objects and

Future of Moore's Law

Chip design

Transistors

- SiGe
- FinFFT
- INT
- Chip stacks (3D hybrid)
 - Intel/Micron 3D Xpoint
- 🗖 3D
 - NAND Flash (EEPROM)
- ✤ Architecture
 - Specialized hardware (GPU, APU, et²)
 - Reconfigurable hardware (FPGA)
- Thermal/Cooling
 - Microfluidics (liquid cooling)
- Something completely different
 - Molecular computing
 - Quantum computing

"As Moore's Law slows, we are being forced to make tough choices between Power, Performance and Cost." (ARM)



A transistor is a switch. Ordinarily, current cannot flow. When a voltage is applied to the gate, the channel becomes conductive, current flows from the source to the drain, and the transistor switches on.

A finFET transistor raises the channel above the block of silicon upon which the device sits. That allows the gate to wrap around three sides of the channel, improving its electrical properties.

Gate

Drain

Dr Jeff

Jeff Drobman ©2016-23

Source: The Economist

New sorts of transistors can eke out a few more iterations of Moore's

law, but they will get increasingly expensive

Faith no Moore

Selected predictions for the end of Moore's law



Sources: Intel; press reports; The Economist

TSMC on Moore's Law






























Moore's Law vs actual transistor count Prediction of Moore's Law 27,717,971,082 23,600,000,000 Graphcore GC2 IPU (CPU) 21,100,000,000 Nvidia GV100 Volta (GPU) A. 19,200,000,000 AMD 32-core Epyc (CPU) 18,600,000,000 Nvidia TU102 Turing (GPU) 18,000,000,000 Qualcomm Centriq 2400 (CPU) 15,300,000,000 Nvidia GP100 Pascal (GPU) 13,280,000,000 AMD Vega 20 (GPU) 12,500,000,000 AMD Vega 10 (GPU) 11,800,000,000 Nvidia GP102 Pascal (GPU) 10,000,000,000 Apple A12X Bionic (CPU) 10,000,000,000 Oracle 32-core SPARC M7 (CPU) 9,700,000,000 IBM z14 Storage Controller (CPU) Nvidia Tegra Xavier SoC (CPU) 9,000,000,000









4.5 – 5 GHz

Even with Moore's Law continuing apace, have we reached a plateau where, unless you have a special need like gaming or animation, a 3to6 year old desktop or laptop is good enough for most users? Has the innovation shifted to phones and tablets?



Jeff Drobman, Lecturer at California State University, Northridge (2016-present) Answered just now

Moore's Law has indeed slowed to a crawl over past serveral years. we see that CPU frequency has plateaued to about 4.5 GHz. performance has been gained by adding cores, incl specialized cores like GPU, NPU.

Performance Factors



Will computing stop improving when Moore's law ends?



Jeff Drobman, Lecturer at California State University, Northridge (2016present)

Answered just now

yes and no. an individual core (CPU or GPU) will not have its integer scalar performance increase. but "ILP" can be applied to cores, along with parallel data as vectors or matrices. achieving greater degrees of parallelism (in both hardware and software) is the fertile ground for performance increases.



Intel's View of Moore



Nov 2021 -

Intel CEO Gelsinger just claimed Intel will exceed this rate!





Arm Shows Backside Power Delivery as Path to Further Moore's Law

Delivering power to devices from the other side of the silicon will enable smaller processors

Chips











Q

Biden zeroes in on chip shortage

Chip Shortage: SEMI

MILPITAS, Calif. - April 1, 2021 - SEMI, the industry association serving the global electronics design and manufacturing supply chain, today applauded the inclusion of initiatives to strengthen U.S. semiconductor manufacturing and research and calls for investment in the Biden Administration's American Jobs Plan. In addition to calling on Congress to invest \$50 billion in semiconductor manufacturing and research, in line with the bipartisan CHIPS for America Act, the plan lists semiconductors as a field of focus in its call for an investment of another \$50 billion in the National Science Foundation (NSF).

"Reversing the 50% decline in the U.S. share of semiconductor manufacturing capacity over the past 20 years requires bold action, and the Biden administration's support for significant funding to bolster the industry in its American Jobs Plan is an important step forward," said Ajit Manocha, SEMI president and CEO. "Funding the authorized CHIPS For

America Act provisions and enacting an investment tax credit to support investment in the U.S. semiconductor supply chain will make the United States a globally competitive location for new semiconductor facilities. The plan's focus on addressing workforce development in the industry is encouraging as well, as the competition for talent is intensifying to support projected growth."

About SEMI

SEMI^{*} connects more than 2,400 member companies and 1.3 million professionals worldwide to advance the technology and business of electronics design and manufacturing. SEMI members are responsible for the innovations in materials, design, equipment, software, devices, and services that enable smarter, faster, more powerful, and more affordable electronic products. Electronic System Design Alliance (ESD Alliance), FlexTech, the Fab Owners Alliance (FOA) and the MEMS & Sensors Industry Group (MSIG) are SEMI Strategic Technology Communities, defined





Intel CEO on Chip Shortage

ON THE EARNINGS CALL PAT GELSINGER, INTEL CEO



"The unprecedented demand for semiconductors has stressed supply chains across the industry. We've doubled our internal wafer capacity in the last few years, but the industry is now challenged by a shortage of foundry capacity, substrates, and components..."

Intel building 2 new fabs in AZ **\$20B**

"...We expect it will take a couple of years for the ecosystem to make the significant investments to address these shortages." Intel, Micron only remaining US fabs

- Intel produces 17% of world supply
- US produced 37% 20 yrs ago
- AMD divested its 25 fabs in 2006











Intel Automated Fab





Intel Automated Wafer Test



Chips





Semiconductors: Si, Ge







Related Why is silicon mostly used in tech companies than germanium?

The earliest semiconductor devices were made of germanium. This started to change when the first planar IC's were developed. It is easy to grow a stable, insulating oxide film on silicon but not on germanium, so silicon was the material of choice. One of the key breakthroughs in silicon processing was made by Andy Grove and a colleague: the Grove-Deal model of SiO2 growth kinetics.

These days, most advanced devices have channels made of an alloy of Si and Ge doped with boron (SiGeB). The percentage of Si and Ge is carefully controlled and varied over the height of the channel to produce strain which enhances the mobility of electrons or holes.

Silicon Crystal Ingot (Boule)



Wafers





12" Wafer (2002) (Current Standard)







Wafers





200 And 400 mm wafers

Die on a Wafer



Intel Pentium



Intel Pentium microprocessor die and wafer



Wafers





Quora





After taking into consideration the wasted dies intersecting the "Exclusion Edge" there are a possible 577 dies produced. In this sample, 392 have defects of some sort, leaving only 185 that can be used as intended.

Assuming these are CPU dies with integrated GPU, any defect in a GPU region can result in a CPU with the GPU disabled and be sold at a lower price. If this is a die with six CPU cores, one pair of cores can be disabled to make it a quad core. In that way, maybe half of the defective chips can be salvaged.

With say 14nm production there are fewer transistors per die, and thus a lower probability of defects as compared to 7nm production. The defect rate goes up because there simply are a lot more transistors and a lot more opportunities for a defect to occur.

The problem is greatly compounded when the die is quite large, because then the possible number of good dies per wafer goes down and the probability of getting defects goes up. GPU dies like those made by Nvidia are easier to bin because multiple compute units can be disabled and still result in a perfectly functional product.

Just as a case in point. A RTX 2080 has 46 compute units, while a RTX 2060 KO has only 30. But they both use the same TU104 silicon. The 2060 KO edition has a whopping 16 of its compute units disabled. Fully 1024 of its GPU cores are dead. You simply can't do that with CPU silicon.

Quora





X



Angus Mccamant · Follow

Former Device Physics Semiconductor ICs, Metrology · Jul 3

Related How many chips can be fabricated on a wafer? How much do companies pay per chip when buying from semiconductor fabrication plants (fabs)?

The number of chips on a wafer is determined by the chip size. Most modern fabs use 300mm wafers which have about 70,000 square mm. As small chips can be one mm on a side for a square chip you could get 70,000 chips on one wafer.

There are complications. All wafer fabs have test devices on wafers for monitoring the process. A finished 1mm per side chip also has to have room for sawing the wafer into individual chips. The width of the saw blades results in about 100 microns (0.1mm) mandatory spacing between chips. In real life you will get more like 50,000 one mm chips on a wafer.

The fabs do not sell chips, they sell wafers. There is a minimum wafer lot size you have to order for your custom design. This results in a huge up front cost, millions of US dollars, for all the tooling, masks and prep work done to get the design ready for the fab. Many fabs, including TSMC, regularly run project wafers where you purchase only a small portion of a wafer. This will avoid much of the fixed cost as it can be shared by tens of customers. Most fab customers will run prototype chips on multiple customer project wafers before committing to buying wafer lots.

Intel Core i7 Die



Hennessy & Patterson

Figure 1.5.2: A 12-inch (300mm) wafer of Intel Core i7 (Courtesy Intel) (COD Figure 1.13).

The number of dies on this 300 mm (12 inch) wafer at 100% yield is 280, each 20.7 by 10.5 mm. The several dozen partially rounded chips at the boundaries of the wafer are useless; they are included because it's easier to create the masks used to pattern the silicon. This die uses a 32-nanometer technology, which means that the smallest features are approximately 32 nm in size, although they are typically somewhat smaller than the actual feature size, which refers to the size of the transistors as "drawn" versus the final manufactured size.



Wafer





Wafers: Yield





yellow shows bad dice (a function of defect density)

Wafer Fab









Process Nodes



Structure of a MOSFET in the integrated circuit.





MOS Transistor




MOS Transistors







MOS Transistors



The channel will have a length (distance from one electrode to the other) and a width (imagine this diagram coming out of the screen). The electrodes have geometries. The gate doesn't always span the full width of the channel and is its own critical dimension.

The sizes of each of these things are critical dimensions. They all have an effect on the performance of the device because they will contribute parasitic capacitance and resistance. Parasitic capacitances



Parasitics depicted by University of New Mexico 🖄



The first thing to note is that the gate length (L_g) is 16.5nm. The width of the gate will vary, but I am going to go out on a limb and guess it is no smaller than $3W_{\rm fin}$, or 18nm. And the overall structure is tall: 52nm plus another few nm

New Processes











Images of IBMs 2nm Chip architecture

TSMC Making 3nm



12-2-21

TSMC Begins Pilot Production of 3nm Chips: Report

By Anton Shilov 3 days ago

TSMC's N3 enters risk production.

Taiwan Semiconductor Manufacturing Co. has started risk production of chips using its N3 (3 nm-class) fabrication process, two reports from Taiwan read. As usual, it will take the contract maker of chips and its partners several quarters to polish off the technology and designs before both enter high-volume manufacturing (HVM).

TSMC initiated pilot production of N3 chips at its Fab 18 at the Southern Taiwan Science Park near Tainan, according to reports from DigiTimes and TechTaiwan. HVM of chips using the new node will commence in the second half of the year, but since cycle time for the new process is over 100 days, the first N3 chips made by TSMC will ship in early 2023.

TSMC





Flip-Chip MCM

InFO_SoW



Fig. 2. Electrical performance comparison between Flip-Chip MCM and InFO_SoW

TSMC



This breaks through the current barriers with multi-chip modules. With an interposer-based technology such as Nvidia datacenter GPUs, they are limited by interposer manufacturing limits. TSMC's 5th generation CoWoS-S recently went into mass production with interposers that are 3x the reticle limit. The reticle limit is 26mm by 33mm and is associated with the maximum area a lithographic machine can pattern in one instance. This method involves reticle stitching and other manufacturing difficulties because the interposer is a silicon chip itself. This type of packaging has limitations in scaling the number of chips for huge AI workloads.

	Flip-Chip MCM		InFO_SoW
	Cold Plate Chip1 Chip2 Chip3 Chip4 Substrate PCB PDN Current	Power Supply P G t Path	External connections Power Distribution and Connectivity Chip 1 Chip 2 Chip 3 Chip 4 Thermal module
Line width / space (µm)	10/10		5/5
Line density	1x		2x
Bandwidth density	1x		2x
PDN impedance	1x		0.03x

Fig. 2. Electrical performance comparison between Flip-Chip MCM and InFO_SoW

Process Timeline



Recent Timeline:

2018 - Apple ships first 7nm consumer processor (TSMC), AMD later follows suit (TSMC), Intel stuck on 14nm. Samsung debuts 7nm.

2019 - Samsung and TSMC both begin offering 5nm. TSMC samples Apple5nm processors.Apple

2020 - Apple ships first 5nm consumer processor (TSMC), AMD expected to follow soon. Intel begins shipping 10nm (laptop) processors in earnest, desktop 10nm expected before 2021.

From 5nm it goes: $5nm \rightarrow 3nm \rightarrow 2.1nm \rightarrow 1.5nm \rightarrow 1.0nm = 4$ shrinks left. [IRDS roadmap: IEEE Releases Expansive 2018 Roadmap for Devices and Systems 2]

Remember the marketing problem? Intel Intel's 10nm process is considered to be comparable with TSMC's 7nm process. So Intel's roadmap may be a little more indicative of how many shrinks we have left.

 $10nm \rightarrow 7nm \rightarrow 5nm \rightarrow 3nm \rightarrow 2.1nm \rightarrow 1.5nm \rightarrow 1.0nm = 6$ shrinks left.

TSMC vs Intel Nodes



Intel Versus TSMC Nodes and Timing

	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027
TSMC	7	7/7	F	F	2	2	2	2	1 5	1 6	
- Node	/	///+	5	5	3	3	2	2	1.5	1.5	
- Status	Risk	Full									
Intel											
- Node	14	14	10	10SF	10SF	7	7	5	5	3	3
- EN	13.8	13.8	7.1	7.1	7.1	4.1	4.1	2.4	2.4	1.3	1.3
- Status	Full	Full	Full	Full	Full	Ramp	Full	Ramp	Full	Ramp	Full

- Risk = risk starts, Ramp = production ramp, Full = full production, EN = TSMC equivalent node.
- TSMC is assumed to stay on a new node every two years with shrink similar to the 5nm and 3nm announced shrinks.
- Intel 5nm and 3nm are assumed to be on two year intervals and to be 2x density improvements consistent with the announced 7nm density shrink.



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TSMC vs Intel Nodes



TSMC Nodes

- TSMC nodes versus transistor density.
- 28nm through 5nm are actual.
- 3nm is projected based on TSMC announcements.
- 2nm and 1.5nm are IC Knowledge projections.





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Semicon News





Tesla at TSMC





Fig. 10. InFO_SoW system assembly demonstration

This image looks remarkably similar to the Tesla chip and offers some insights. Just like the tesla image, there is a cold plate. Various chips arrange in a grid, an InFo Wafer, and connectors. The structures look to be a 1 to 1 match but the exact details them look to be slightly different than the initial TSMC research.

Tesla at TSMC



TSMC's Chiplets Integration

TSMC

Tesla AI Day Supercomputer Chip Teaser | Is This The First Deployment Of TSMC InFO_SoW? by Dylan Patel on 08-08-2021 at 10:00 am

Categories: Events, Samsung Foundry, TSMC



At first glance it looks like there is a carrier, heatsink, and power delivery. The most interesting part of course, is the chips. It has a large array of BGA solder pads and a 5×5 array of chips. This type of packaging looks incredibly unorthodox and the only thing we can think of is TSMC's integrated fan out system on wafer technology (InFO_SoW). Here is the link to the paper on IEEE.

Chip Cooling



physicsworld

semiconductors and electronics

Q

SEMICONDUCTORS AND ELECTRONICS RESEARCH UPDATE

New semiconductor cools computer chips

05 Aug 2021 Isabelle Dumé

A novel semiconducting material with high thermal conductivity can be integrated into highpower computer chips to cool them down and so improve their performance. The material, boron arsenide, is better at removing heat than the best thermal-management devices available today, according to the US-based researchers who developed it.

BAs = boron arsenide

III-V semi

Chip Cooling



physicsworld Q

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An electron microscopy image of a gallium nitrideboron arsenide heterostructure interface at atomic resolution. Courtesy: The H-Lab/UCLA

The size of computer chips has been shrinking over the years and has now reached the nanoscale, meaning that billions of transistors can be squeezed onto a single computer chip. This increased density of chips has enabled faster, more powerful computers, but it also generates localized hot spots on the chips. If this extra heat is not dealt with properly during operation, computer processors begin to overheat. This slows them down and makes them inefficient.

Defect-free boron arsenide

Researchers led by Yongjie Hu at the University of California, Los Angeles, recently developed a new thermal-management material that is much more efficient at drawing out and dissipating heat than other known metals or semiconducting materials such as diamond and silicon carbide. This new material is known as defect-free boron arsenide (BAs), and Hu and colleagues have now succeeded in

interfacing it with computer chips containing wide-bandgap high-electron-mobility gallium nitride (GaN) transistors for the first time.





Metal Interconnect

Metal Interconnect



Quora

Aluminum \rightarrow Copper \rightarrow Cobalt

Jeff Drobman, Lecturer at California State University, Northridge (2016present)

a little elaboration. the top layer of all IC's have been the metal interconnects, which have gone from 1 layer to 4 layers to 8 or more — similar to PCB's. aluminum has been used due to cheap and easily vaporized for vapor deposition through masks. copper is a better conductor, but more expensive and harder to deposit. a few manufacturers have used copper, such as IBM. Note that the metal pitch has to match the transistor pitch (now about 10–14nm).



Jerry Coffin · 25m ago

Copper interconnect was introduced 25 years ago, and has been in widespread use for over 20 years now. Intel recently started using Cobalt for the first couple of layers.

As far as layer count goes: around a dozen is now pretty common.

🔰 Jeff Drobman 🔦 · Just now

thank you for the information. I know copper was first used in the 1980's, with IBM a leader. I don't think it has ever been "widespread", with aluminum being the bulk of use. I have not heard of cobalt being used for metal, and I don't understand why it would: cobalt is more than 2x the resistivity of aluminum (62.4 to 26.5 nOhm-m). maybe it is used for its hardness against heating?

Quora Metal Interconnect



Aluminum \rightarrow Copper \rightarrow Cobalt



Metal Interconnect Quora



Aluminum \rightarrow Copper \rightarrow Cobalt

The transistors connect to each other using metal wires called interconnects. There are several layers of them (more then 8). Usually the space between them is filled with an insulator to provide structural rigidity, and expel air which can expand when heated and damage the chip, but IBM very kindly took the insulator out of one of their chips to show what the interconnect looks like:



Quora Metal Interconnect



Aluminum \rightarrow Copper \rightarrow Cobalt

This is cross section of an old school planar transistor. Intel now uses 3D transistors called Fin-FETs which look like this:



TSMC is getting there with this:





lora

Metal Interconnect



Aluminum \rightarrow Copper \rightarrow Cobalt

Cobalt is already used as a copper barrier layer. What's unique with Intel is using it as a conductor for an entire metal layer.

The main reason for cobalt over copper is that at ~20 nm pretty much all materials stop behaving like their macroscopic forms with dimensions above 20 nm in terms of physical properties. This is a large part of what "nanotechnology" is about exploiting: everything changes at low nanometer scales of physical dimension.

The reasons are that grains and crystal structures start to reach their limits as "statistical mechanics "d"-described materials and they transition to being primarily described by only pure quantum mechanics d. Mathematically this is a huge transition. And in terms of control of outcomes, it's also huge.

So it turns out that copper ceases being "one of the best electrical conductors" at these dimensions. And somewhat bizarrely, cobalt is better. Even when at macroscopic (human dimension) sizes, cobalt is not a particularly good electrical conductor. Not bad but there's a long list ahead of it (copper is 5x more conductive than cobalt in macro-scale dimensions):



Quora

Metal Interconnect



Aluminum \rightarrow Copper \rightarrow Cobalt

But now we are at physical dimensions of ICs where this nanoscale difference becomes important so it's out with copper and in with cobalt if you want to achieve thinner metal lines.

But why is that only now a problem? Here's the dirty little secret about metal lines: even in a 7 nm process, the metal interconnects are generally equal or larger than 30 nm. You can see this fact in this electron microgram:





iora

Metal Interconnect



Aluminum \rightarrow Copper \rightarrow Cobalt



I've added the approximate location and size of a transistor's key terminals. They are actually smaller at the labeled scale but I was at single pixels in the original image.

The main reason for have 9 levels of metal is because of this line width limit and how it limits packing density. At the bottom you can "see" the transistors being tiny and existing

Instead you need to "cross over" other metal lines more to achieve decent packing density. And to do that you need more metal layers that are wider and wider (as power supply currents accumulate under Kirchoff's Current Law).



Quora

Metal Interconnect

Aluminum \rightarrow Copper \rightarrow Cobalt





So simply having a 7 nm transistor does NOT mean you can actually pack everything as tight as you want/like (to 7 nm or some smallish multiple between transistors, for example). The metal lines minimum dimensions dictate how tight you can actually pack things. And that minimum dimension is limited by a failure mode called electromigration 2.



lora

Metal Interconnect



Aluminum \rightarrow Copper \rightarrow Cobalt

So simply having a 7 nm transistor does NOT mean you can actually pack everything as tight as you want/like (to 7 nm or some smallish multiple between transistors, for example). The metal lines minimum dimensions dictate how tight you can actually pack things. And that minimum dimension is limited by a failure mode called electromigration 🗹.

And this density problem what Intel is trying to address with full cobalt Metal 1 (the lowest bottom metal). Cobalt is better behaved and gives better performance below 20 nm line widths. Copper won't cut it.

Except switching a material so radically is really, really hard because now you have new issues. Primarily reliability issues: i.e. how long will the material remain operating and positioned as originally manufactured assuring the same performance years later as the first day it was made. The real world is not a static thing – everything is in constant change though often slowly. You start dying the day you are born!

When we switched to copper from aluminum, numerous new and unexpected failure modes occurring only with copper were discovered which took time to solve/mediate. It's only more difficult once it's no longer a statistical mechanics problem but instead a quantum mechanics problem. Radically more difficult!

Chips







1971 **DIP**

Intel i8008 8-bit MPU





SMT —

Surface Mount Packaging (1980s-1990s)





SMT









Ball Grid Packaging and Chip Scale Packaging (1990s – 2000s)

As the demands of semiconductor speed continue to pick up, so does the need for better packaging. While QFN (quad-flat no-leads) and other Surface Mounted technologies clearly continue to proliferate, I want to introduce you to the beginning of a package design that we will have to know about in the future. This is the beginning of the solder balls – or broadly Ball Grid Array (BGA) packaging.



Those balls or bumps are called solder bumps/balls

Chip Packaging (MCM)





Chip Packaging: 3D Die



3D DRAM die stack

And what's interesting is we have a clear example of an entire semiconductor market that went 3D – Memory. Memory's push into 3D structures is a very good indication of what's to come. Part of the reason why NAND had to go 3D was that they struggled to scale at smaller geometry. Imagine memory as a large 3D skyscraper, and each of the floors is kept together by an elevator. These are called "TSV"s or Through silicon vias.



This is what the future looks like, and it's even possible we will be stacking GPU/CPU chips on each other or stacking memory on CPU. This is the final frontier

Chip Packaging: 3D Die



TSMC

A Quick Overview of 2.5D/3D Packaging

TSMC's CoWoS

This is seemingly the workhorse of the 2.5D integration process and was pioneered by Xilinx.



Chips



Wafer Fabs Foundries
Foundries Supply Chain





Harvey King

born in Taiwan, grew up in US, family rooted in mainland China for centuries.



Fab Timescales

SEMICONDUCTOR INDUSTRY ASSOCIATION

Α





Wafer Fabs Today



- 1960 🛠 IBM
- 1968 🛠 Intel
- ¹⁹⁷⁸ * Micron**
- 1980 🛠 Samsung
- 1987 ***** TSMC* (1st foundry)
- ²⁰⁰⁹ ❖ AMD → Global Foundries*

*Pure Foundry

**Internal use only

Foundry Stats 2020





Foundry Shares 2Q22





TSMC 3Q22



Revenue = \$20.23B
 EPS = \$1.79
 Wafer revenue shares

 5nm = 28%
 7nm = 26%

Samsung **7nm** did pretty good but Samsung **5nm** and **4nm** had serious PDK/yield problems and Samsung **3nm** is not really competitive against TSMC N3 and it requires new design considerations for **GAA**.

WW Fab Share by Region





Source: LA Times/SIA 1/22/22

WW Fabs





WW Foundries



September 2020 By Antonio Varas, Raj Varadarajan, Jimmy Goodrich, and Falan Yinug

Global manufacturing capacity by location (%)



WW Foundries



September 2020 By Antonio Varas, Raj Varadarajan, Jimmy Goodrich, and Falan Yinug

Evolution in manufacturing-process node

No. of transistors per microprocessor, performance and cost



Foundry Biz





Foundry Wafer Capacity Share

Chips/Fabs



Chip Fab: Mask Making ASML



Quora ASML EUV Machines



Current EUV lithography system (NA=0.33) (front) compared to the next generation of high NA EUV lithography system (NA=0.55) (back).



Quora ASML EUV Machines



ASML: EUV for Mask Litho Jeff Drobman ©2016-23

Semiconductor Advisors



Is ASML Immune from China Impact? by Robert Maire on 10-21-2022 at 10:00 am Categories: China, Lithography, Semiconductor Advisors, Semiconductor Services

ASML proves litho's place at Apex of semiconductor food chain

ASML announced a great quarter with Euro5.8B in revenue and EPS of Euro4.29/share. Outlook is for revenues of Euro6.1B to 6.6B with gross margins of 49%. Gross margin for 2022 will come in about 50% overall.

Most importantly, orders came in at a huge Euro8.9B, 77% logic, bringing backlog to a multi-year Euro38B. ASML is looking at shipping 60EUV and 375DUV systems in 2023, assuming supply chain issues are resolved.

ASML: EUV for Mask Litho Jeff Drobman ©2016-23

Semiconductor Advisors



Is ASML Immune from China Impact? by Robert Maire on 10-21-2022 at 10:00 am Categories: China, Lithography, Semiconductor Advisors, Semiconductor Services

China immunity from two factors

ASML will have 5% or less impact next year from the China issue for two simple reasons; number one, the majority of current business is non leading edge, above 14NM as ASML was already not shipping any EUV tools to China. Number two, ASML is sold out anyway and there are a large number of customers who will happily snap up any systems that China doesn't or can't take.

In our view, as we had previously commented on months ago, ASML is virtually immune to China embargo issues given their leading positioning in the industry. The semiconductor industry remains a zero sum game and litho systems not shipped to China will go elsewhere to satisfy demand.

ASML: EUV for Mask Litho



Semiconductor Advisors

Is ASML Immune from China Impact? by Robert Maire on 10-21-2022 at 10:00 am Categories: China, Lithography, Semiconductor Advisors, Semiconductor Services

Light source technology is developed by former Cymer, in San Diego, that ASML was allowed to buy by the US government. We are relatively certain that there were agreements regarding Cymers technology in order to win acquisition approval.

Many investors may not be aware that much if not most of the laser technology, especially for EUV, arose out of the "star wars" laser weapons systems of the Regan era as Cymer employed many scientists out of the ex star wars program from both the US and former Soviet Union. The technology used in the 250KW drive laser in EUV systems could be re-purposed for military applications.

77% logic mix shows resilience

The fact that 77% of orders are from logic suggests that a more rapid slowdown in memory will not impact ASML at all. Management also announced orders for High NA systems along with regular EUV systems. Though high NA was not broken out, at over Euro300M a system, the numbers can add up more than twice as fast as DUV systems. We assume that TSMC, Intel and Samsung have likely already ordered multiple High NA EUV systems. TSMC's recent capex cut clearly is not impacting their litho system orders as they understand the import of leading in litho.

Quora ASML EUV Roadmap



EUV product roadmap

Wavelength	NA, Half pitch	2020 2021 2022	2023 2024 ≥2025			
EUV	0.33 NA, 13 nm	NXE:3400C 1.5 nm 135 wph ¹ / 145 wph ² 1.1 nm 160 wph	NXE:3800E NXE:4000F <1.1 nm >195 wph / 220 wph ² <0.8 nm >220 wph			
	0.55 NA, 8 nm		EXE:5000 at ASML fab <1.1 nm 150 wph ³ <0.8 nm 220 wph			
		ASML	Wafers/hours (wph) are at dose 30mJ/cm ² unless specified otherwise. 1) 170wph@20mJ/ cm ² 2) Including throughput upgrade 3) 185wph@20mJ/ cm ² Product: Matched Machine Overlay (nm) Throughput (wph) Product status: Released Development Definition			
ASML		SPIE, ADVANCED High NA, see: SPIE 12051-6 High NA EUV enabling cost efficient scaling for N+1 t	technology nodes, Greet Storms et al. Page 15 Debie			

Figure 5. System Roadmap.

ASML EUV Mask Count



High NA keeps number of masks & cycle time acceptable

Repetition of adoption of EUV technology



Figure 8. Mask Count Trends.



Figure 2. Number of EUV Wafers Exposed.

Chips/Fabs



Chip Design/Fab AMD/Intel

Fabs – AMD, Intel





AMD Sunnyvale Fab 1 1970



Cost x10,000 in 40 years averages to 250x per year



Intel's latest Fab in Hillsboro



An aerial view of Ronler Acres, Intel's largest silicon research and development hub.

Chip Fab





Bob McConnell

Former VP and Site Manager, Heilbronn, Germany at Atmel (company) (2003–2009) \cdot Wed

Silicon wafer chip defects are said to happen on all chips produced. How/why does this occur, and are there ways to prevent it?

First, read Wikipedia: Semiconductor Device Fabrication. I think it explains the issues at a basic level. Secondly, there are many places for defects to occur. They DO NOT occur on the basic patterning information because that is computer generated. If it doesn't check out correctly the pattern is regenerated. The wafer can have defects due to crystal growth anomalies. This is very unlikely and causes negligible failures.

Particles are at a very low level. The wafers being processed are moved between process steps in sealed, super clean boxes. The boxes are only opened inside machines that are sealed and or have positive pressure. X

Chip Fab





Bob McConnell

Former VP and Site Manager, Heilbronn, Germany at Atmel (company) (2003–2009) · Wed

The processing of a wafer involves deposition or growth in various ways of well over a hundred or more layers of material. This includes photoresist to be exposed as part of the photo lithography process, oxide layers that are grown to be later patterned and etched, metal layers to be patterned and have the interconnect defined, and dielectric layers to be insulators between the metal layer. The dielectric layers are patterned to produce the interconnect between metal layers.

Any of these layers might have a defect caused by a flaw in the material or by a particle that somehow escaped all the controls and filters. The processes are adjusted to, as much as possible, eliminate these defects. A photo layer might be processed twice through a photo lithography step. There might be a high temperature step to allow a material to flow and close a defect. (only works when that high temp doesn't hurt any thing below the current layer) This has been the basic fight of the industry to keep allowing transistor counts to increase. Looking out 4 years and doing some math tells the process engineer and equipment engineer what has to happen to stay on that exponential curve of Moore's Law.

Chip Design vs Mfg



Is designing computer chips the same as planning how to manufacture them?



Jeff Drobman, Lecturer at California State University, Northridge (2016-present) Answered just now

there are many levels of design for all digital systems, including hardware and software. chips have CPU cores, GPU cores, cache memories, I/O, system logic and clocking, etc. first level is the "macro" architecture: layout of all those subsystems. Cores may be licensed (designed by others) or designed from scratch. other subsystems are usually licensed from the fab or others.

It is the design of the cores and other subsystems that is the most intricate design process. Each item needs to follow the detailed "design rules" given by the selected fab (manufacturer), as well as their interconnections.

Al in Chip Design



8

8-31-21



Chuck Bluestein, A great deal of non-fiction reading.

Answered 34m ago

Here is an article that talks about this that you can read and share with others. The name of the article is:



Opinion: Computer chips are getting so advanced, companies are using artificial intelligence to make them

The introduction of AI in chip design is a necessity for performance an...

 ${\mathscr S} \ {\tt https://www.marketwatch.com/story/computer-chips-are-getting-s...}$

This is what the article says on it:

Thanks to a machine-learning technique known as reinforcement learning , artificial intelligence completed the task in only six hours, compared with weeks by humans.

Foundries





Founded 1968

Intel Fabs



Fab name 🕈	Fab location	Production start year •	Process (wafer, node) •			
D1B	USA, Oregon, Hillsboro	1996	300mm, Development			
RB1	USA, Oregon, Hillsboro	2001	300mm, Development			
D1C	USA, Oregon, Hillsboro	2001	300mm, Development			
RP1	USA, Oregon, Hillsboro	2001	300mm, Research			
D1D	USA, Oregon, Hillsboro	2003	300mm, Development			
D1X SA, Oregon, Hillsboro		2013	300mm, Development			
Fab 11X SA, New Mexico, Rio Ranch		1995 upgrade 2020/2021 with 22/14	300mm, 45 nm/32 nm, Packaging			
Fab 12	USA, Arizona, Chandler	2006	300mm, 22 nm/14 nm/10 nm			
Fab 22	USA, Arizona, Chandler	2002	300mm, 22 nm/14 nm/10 nm			
Fab 24	📕 🧧 Ireland, Leixlip	2006	300mm, 14 nm ^[2]			
Fab 28a	💿 Israel, Kiryat Gat	1996	300mm, 22 nm			
Fab 28	💽 Israel, Kiryat Gat	2023	300mm, 22nm/14nm/10nm ^{[3][4]}			
Fab 38	💼 Israel, Kiryat Gat	2024	300mm, 22 nm ^[5]			
Fab 32	USA, Arizona, Chandler	2007	300mm, 22 nm/14 nm/10 nm			
Fab 34	📕 📕 Ireland, Leixlip	2023	300mm, 7 nm ^[6]			
Fab 42	USA, Arizona, Chandler	2020	300mm, 10 nm/5 nm (2024)			
Fab 52	USA, Arizona, Chandler	(2024)[7]	300mm, 7 nm			
Fab 62	USA, Arizona, Chandler	(2024)[7]	300mm, 5 nm			
	USA, Ohio, Licking County	(2024-2025)	300mm, 5 nm			
SC2	USA, California, Santa Clara		Reticle/Masks, Intel Mask Operations[8]			
	Malaysia, Kedah, Kulim	(2024)	300mm, Packaging ^[9]			
	Germany, Magdeburg, Saxony-Anhalt	(2027)	[10]			
	Italy	(2025-2027)	300mm, Packaging ^[11]			

Chip Shortage







Intel New Fabs



Intel Breaks Ground on Two New Leading-Edge Chip Factories in Arizona

S Daniel Nenni · ③ Today at 5:44 AM



Today at 5:44 AM

New \$20 billion capacity expansion will bring Intel's total Arizona investment to more than \$50 billion.

Intel CEO Pat Gelsinger signals to the crowd from earth-moving equipment in Chandler, Arizona, on Friday, Sept. 24, 2021, for a groundbreaking ceremony to celebrate the largest private-sector investment in Arizona's history. The construction of two new computer chip factories is a \$20 billion project that will bolster U.S. semiconductor leadership and help bring geographical balance to the global supply chain. (Credit: Intel Corporation)



∞ ‡

Intel New Fabs



September 24, 2021 03:21 PM Eastern Daylight Time

CHANDLER, Ariz.--(BUSINESS WIRE)--What's New: Intel today broke ground on two new leading-edge chip factories at the company's Ocotillo campus in Chandler, Arizona. In a groundbreaking ceremony attended by senior government officials and community leaders, Intel CEO Pat Gelsinger celebrated the start of construction on the largest private investment in state history and reiterated the company's commitment to investing in U.S. semiconductor leadership.

"Today's celebration marks an important milestone as we work to boost capacity and meet the incredible demand for semiconductors: the foundational technology for the digitization of everything. We are ushering in a new era of innovation – for Intel, for Arizona and for the world. This \$20 billion expansion will bring our total investment in Arizona to more than \$50 billion since opening the site over 40 years ago. As the only U.S.-based leading-edge chipmaker, we are committed to building on this long-term investment and helping the United States regain semiconductor leadership."

-Pat Gelsinger, Intel CEO

Why It's Important: Advanced domestic chipmaking capacity and capabilities are critical for the sake of both economic and national security. The United States has lost ground in semiconductor manufacturing and is at risk of falling farther behind. With its new IDM 2.0 strategy, Intel is doing its part to help rebuild U.S. leadership and bring more balance to the global supply chain. Intel is the only semiconductor manufacturer with leading-edge process and packaging research capabilities in the United States, and the company is investing in domestic capacity to support the surging worldwide demand for chips across multiple segments, from PCs to automobiles to the data center and more.

Intel New Packaging



Intel's Heterogenous System-in-Package Examples



Intel Agilex[™] (FPGA) EMIB Technology



Intel Meteor Lake (Client) Foveros Technology



Intel Granite Rapid (Server) EMIB Technology



Jeff Drobman ©2016-23

Ponte Vecchio – X^e (HPC) EMIB+Foveros Technologies

Heterogenous Packaging Technology Enabling Products Across All Market Segments

Assembly and Test Technology Development

Intel Confidential

intel. 53

Sapphire Rapids is slated to be the first lineup from Intel to adopt the chiplet (MCM) or tiled design (plus some SKUs using on-die HBM) and Granite Rapids refining it. The former is expected to feature up to four (15-core, 1 disabled) tiles, resulting in a total core count of 56.

Intel New Processes





Intel's New Foundry Strategy (Colored

The central tenants of IDM 2.0 for Intel are:

- Utilize the Intel internal factory network to build the majority of Intel's products internally.
- Expand use of foundries so that all products have some level of foundry production.
- Increasing engagement with TSMC, Samsung, GLOBALFOUNDRIES (GF) and UMC.
- Plan to be a major foundry with US and European based manufacturing to balance the reliance on Asia.

There was slide that showed something like 80% of leading edge in Asia centered around Taiwan and South Korea, 15% in the US and 5% in Europe.

Intel's New Foundry Strategy eff Drobman

Intel is said to have made a \$2B takeover offer for chipmaker SiFive?!?!?

≥ Daniel Nenni · ③ Thursday at 11:51 AM



Thursday at 11:51 AM

A D M I N Staff member Intel is said to have offered to purchase SiFive for more than \$2B. SiFive, a designer of semiconductors, has been talking to its advisors to see how to proceed, according to a Bloomberg report, which cited people familiar. SiFive has received multiple bids from other interested parties and has also received offers for an investment. SiFive last raised more than \$60M in a Series E financing round last year and was valued at about \$500M, according to PitchBook. In June 2019, Qualcomm (NASDAQ:QCOM) participated in a \$65.4M Series D round for SiFive, a fabless semiconductor company building customized silicon based on the open RISC-V instruction set architecture.

∝ #1

Wow, great move if it is true. If Intel wants to get into the foundry business doing turnkey ASICs is definitely the way to go. Intel already acquired eASIC. That way Intel can closely control and protect IP and make sure designs/chips are done the Intel way, absolutely.

The ASIC business has changed quite a over the last couple of years as fabless chip companies take control (Marvell, Broadcom, and Mediatek). Exciting times in the semiconductor ecosystem, absolutely!

Intel Process Nodes



Slower Node Transitions Versus Foundries

IC KNOWLEDGE LLC

	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023
Intel	14nm					10nm				7nm
Samsung	14nm		10nm		7nm	5nm			3nm	
TSMC		16nm	10nm	7nm		5nm		3nm		2nm?

- Intel takes bigger density jumps but less often.
- TSMC and Samsung take smaller jumps more frequently, 5 nodes versus Intel's 3.



3/24/2021

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4

Figure 4. Node Introductions.
Intel Process Nodes

Figure 3. illustrates Intel's hyper scaling.

Hyper Scaling

- Intel started hyper scaling at the same time that scaling was getting harder.
- 2.5x density improvement for 14nm was 1 year late.
- 2.7x density improvement for 10nm was 2+ years late and still has yield issues.



Moore's Law Leadership, Mark Bohr, Intel Manufacturing Day 2017





Intel MOSFET

Intel video

https://www.youtube.com/watch?v=Z7M8etXUEUU&t=47s

FinFET: 2011



Intel amazed the industry with its aggressive adoption of a new transistor topology at the 22nm process node – the FinFET (also known as the "tri-gate FET").





Gate-All Around (GAA) Ribbon FET: Intel 20A in 2024



To further improve the electrostatic gate control over the channel, another major evolution in the transistor topology is emerging to replace the FinFET. A gate-allaround configuration involves a vertical stack of electrically isolated silicon channels. The gate dielectric and gate input utilize an atomic layer deposition (ALD) process flow to surround all channel surfaces in the stack.

Intel will be releasing their GAA *Ribbon FET* 20A process in 1H 2024.







Intel's Newest Fabs

\$20B in Ohio Online end of 2025

SATURDAY, JANUARY 22, 2022 A9

Intel to build chip factories in Ohio

Company will invest \$20 billion as a global shortage highlights the risks of reliance on manufacturers in Asia.

Samsung in Texas

Chipmakers are diversifying their manufacturing sites in response to the shortages. Samsung said in November that it planned to build a \$17-billion factory outside Austin, Texas.

Micron Technology, based in Boise, Idaho, said it would invest \$150 billion globally over the next decade in developing its line of memory chips, with a potential U.S. manufacturing expansion if tax credits can help make up for the higher costs of American manufacturing. Micron globally

10,000 jobs in Ohio

Two chip factories on the 1,000-acre site in Licking County, just east of Columbus, are expected to create 3,000 company jobs and 7,000 construction jobs, and to support tens of thousands of additional jobs for suppliers and partners, the com-

CHIPS for America Act

Lawmakers have been urging House and Senate leaders to fully fund a law meant to address the semiconductor shortage. They want Congress to fully fund the \$52-billion CHIPS for America Act, allowing for stateside investment in semiconductor factories.

More on Intel's New Fabs



– Semi Wiki

\$52B Chips for America is barely a rounding error

When you assume that the Chips for America act is a one time, one shot disbursement spread over a number of years and a number of companies it becomes clear that its not much against TSMC's spend.

It also does not compare to what China as a whole is spending on semiconductor technology.

Basically the US is being outclassed and outgunned by both China and Taiwan (probably part of China in the not too distant future).

Even if Intel got the whole \$52B it still couldn't keep up as the spend would be over several years. Never mind that only \$10B of the \$52B is for fab projects with a \$3B limit per project. Essentially the \$52B will be spread so thin as to be ineffective versus the focused sharp spend of TSMC.

More on Intel's New Fabs



– Semi Wiki

Can the US fabs being built make a difference?

Intel announced two fabs in Arizona at \$10B each along with TSMC announcing a 5NM fab in Arizona which by the time its operational will be a drop in the bucket trailing edge fab perhaps meant to mollify the US.

Samsung has announced a \$17B in Texas in addition to existing facilities there. It looks like Intel has chosen Ohio for its "megafab" project and Micron is eyeing North Carolina.

While details are scarce, it sounds like the Intel Ohio and Samsung Texas fabs are the most impactful on the US. Samsung would be somewhat less impactful as we assume that bleeding edge technology R&D will continue to be done in Korea making the Texas fab a "fast follower" much as the existing Samsung fab in Texas is today. That leaves Intel Ohio as the only trail blazing R&D facility in the US.

It also remains to be seen if the brain trust in Portland can either be moved or shared with Ohio or if Portland remains the R&D center with Ohio for production.

Intel's New Fab Equip.



EUV from ASML

Intel Places Order for ASML's Extreme Ultraviolet Technology

04:49 AM EST, 01/19/2022 (MT Newswires) -- Intel (INTC) and ASML Holding (ASML) said Wednesday that the US chip maker has placed its first purchase order for ASML's TWINSCAN EXE:5200 extreme ultraviolet high-volume production system. The purchase ... (MT Newswires 04:49 AM ET 01/19/2022)

CHIPS Act in Ohio



Sept 2022



PRES. BIDEN: THE FUTURE OF THE CHIP INDUSTRY WILL BE MADE IN AMERICA





CHIPS Act in Ohio





Intel New Euro Fab



INTEL CORP (INTC) (47.70 -0.01) /

Market Chatter: Intel Reportedly Chooses Germany's Magdeburg as Location for New European Chip Factory

08:22 AM EST, 02/28/2022 (MT Newswires) -- Intel (INTC) has picked the city of Magdeburg in Germany as the location for a new European chip factory, Reuters reported on Saturday, citing an unnamed person familiar with the matter. The US ... (MT Newswires 08:22 AM ET 02/28/2022) Read more

Intel – Italy Deal 8-10-22 Content of SemiWiki.com

Italy, Intel close to \$5 billion deal for chip assembly and packaging factory

I think Intel believes it can manage the cost in Italy that is comparable or cheaper to what other Intel assembly and packaging sites in Vietnam, Malaysia, Philippines, China, and Costa Rica. It's hard to believe it unless it's almost fully automated and use few workers.



Exclusive: Italy, Intel close to \$5 billion deal for chip factory

Italy is close to clinching a deal initially worth \$5 billion with Intel to build an advanced semiconductor packaging and assembly plant in the country, two sources briefed on discussions told Reuters on Thursday.

www.reuters.com

Intel News: Italy Fab



Market Chatter: Intel, Italy Reportedly Pick Veneto Region as Location for Proposed Chip Factory

4:39 AM ET, 09/26/2022 - MT Newswires

04:39 AM EDT, 09/26/2022 (MT Newswires) -- Intel (INTC) and the Italian government have selected the town of Vigasio in the country's Veneto region as the location for a proposed chip factory, Reuters reported Sunday, citing anonymous sources familiar with the matter.

The factory, with an initial investment of some 4.5 billion euros (\$4.36 billion), is part of the company's planned investment of 80 billion euros (\$77.34 billion) to grow capacity in Europe, according to the report.

The new facility is expected to create 1,500 jobs and is slated to start operations between 2025 and 2027, Reuters reported.

Intel to Fab MediaTek



Intel, MediaTek Enter Into Chip-Manufacturing Agreement

5:50 AM ET, 07/25/2022 - MT Newswires05:50 AM EDT, 07/25/2022 (MT Newswires) -- Intel (INTC) said Monday it entered into an agreement with MediaTek to manufacture chips using Intel Foundry Services.

The chipmaker said MediaTek aims to use Intel's process technologies to produce multiple chips for *smart edge* devices.

Financial details of the agreement were not disclosed.



Intel 14th Gen Meteor Lake Rumored To Drop TSMC 3nm Node For tGPU, Might Be Used in 15th Gen Arrow Lake CPUs

Meteor Lake is supposed to be **3 chipsets** - so they'll still need capacity for the I/O die and the iGPU from somewhere. N3 was only to be used for the iGPU where I/O was an older node. This seems like something specific to the iGPU (Intel design not ready) and/or N3 (capacity, timing, etc).

It is neither. *Meteor Lake* is yielding fine: Intel 4 CPU, TSMC N3 GPU, TSMC N5 base die and SoC.

The Open Forum for Semiconductor Professionals

Chips/Fabs



Chip Design/Fab Micron D/SRAM Flash

Micron Fab



DRAM's Moore's Law Is Still Going Strong

Micron Technology pushes ahead with 35 percent density boost and does it without advanced lithography tool

> SAMUEL K. MOORE 1 NOVEMBER 2022





Micron says it is shipping samples of **LPDDR5X** chips, memory made for power-constrained systems such as smartphones.

(LPDDR5X unpacked means: a revved-up twist on the low-power version of the 5th generation of the double data rate memory communications standard, capable of transferring 8.5 gigabits per second.)

It's the first chip made using Micron's new manufacturing process, called 1-beta, which the company says maintains the lead it took a year ago over rivals including Samsung and SK Hynix.



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Micron New US Fabs



Micron Technology Plans US Manufacturing Investments, Welcomes Passage of Chips and Science Act

10:30 AM ET, 07/29/2022 - MT Newswires10:30 AM EDT, 07/29/2022 (MT Newswires) -- Micron Technology (MU) said Friday it plans to invest further in its US memory manufacturing capabilities as the semiconductor company welcomed the passage of the Chips and Science Act in Congress. "The competitive incentives passed yesterday will allow Micron, *the only US-based manufacturer of memory*, to grow domestic production of memory significantly in the years ahead," the company said.

The legislation, which is expected to be signed into law in the coming days, will provide **\$52 billion** in subsidies for domestic chip manufacturers and over **\$100 billion** in technology and sciences investments, according to the Financial Times.

Micron in NY





Chipmaker Micron to build \$20 billion N.Y. factory amid semiconductor boom

Chipmaker Micron to build \$20 billion N.Y. factory amid semiconductor boom

The company eventually could spend up to \$100 billion over 20 years

BY JEANNE WHALEN

OCTOBER 4 AT 11:16 AM

Tech giant Micron said it will invest \$20 billion in a new chip factory in Upstate New York, and up to \$100 billion over twenty years if it decides to expand — another sign of a domestic semiconductor manufacturing boom.

Fabs



Foundries Global Foundries

Founded 2009



PJ11177F C. . .

GlobalFoundries



Major 2021 Accomplishments and Key Fourth Quarter Business Highlights:
In 2021, GF entered into 30 significant long-term customer agreements that provide assurance to our customers and provide revenue visibility to GF.
In 2021, GF broke ground on a new fab on its Singapore campus, expanded capacity in Fab 1 (Dresden) by over 25%, and announced expansion plans for its most advanced manufacturing facility in upstate New York.
GE set a "Journey to Zero Carbon" goal to reduce greenhouse gas emissions by

•GF set a "Journey to Zero Carbon" goal to reduce greenhouse gas emissions by 25% while expanding global manufacturing capacity.

•On October 28, 2021, GF began trading on **Nasdaq** Stock Market under the ticker "GFS."

•In the fourth quarter, GF announced an extension of its wafer supply agreement with **AMD**, increasing the number of chips GF will supply, as well as extending the terms of the agreement to secure supply through 2025.

•In the fourth quarter, **BMW** signed a direct supply assurance agreement with high-tech microchip developer INOVA Semiconductors and GF to secure long-term semiconductor supplies.

•In the fourth quarter, GF and **Ford** announced a non-binding strategic collaboration to advance semiconductor manufacturing and technology development within the US, aiming to boost chip supplies for Ford and the US auto industry.

AMD Orders Wafers



News

ADVANCED MICRO DEVICES (AMD) (154.36 +8.22) /

Advanced Micro Devices to Buy \$2.1 Billion of GlobalFoundries Wafers Under Expanded Deal

10:19 AM EST, 12/27/2021 (MT Newswires) -- GlobalFoundries (GFS) said Dec. 23 that semiconductor company Advanced Micro Devices (AMD) will now buy nearly \$2.1 billion worth of its wafers starting 2022 through 2025 under an expanded deal. A wafer is ... (MT Newswires 10:19 AM ET 12/27/2021)

GlobalFoundries



GLOBALFOUNDRIES / Solutions / Technologies / 12LP 12nm FinFET Technology

12LP 12nm FinFET Technology

Ideal for high-performance, power-efficient SoCs in demanding, high-volume applications

GLOBALFOUNDRIES 12LP platform with 12nm 3D FinFET transistor technology provides best-in-class performance and power with significant cost advantages from 12nm area scaling. 12LP technology can provide up to 75% higher device performance and 60% lower total power compared to 28nm technologies. 12LP was **announced** in 2017 based on GF's proven existing 14nm offering, and the offering has transitioned from 14LPP to 12LP in 2018.

Global Foundries



GlobalFoundries

From Wikipedia, the free encyclopedia

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GlobalFoundries Inc. (**GF**) is a United States-based semiconductor manufacturer headquartered in Malta, New York.^[3] GlobalFoundries was created by the divestiture of the manufacturing arm of Advanced Micro Devices (AMD) and is owned by Mubadala Investment Company.

GlobalFoundries is the world's fourth largest semiconductor manufacturer^{[4][5]} and produces chips for more than 7% of the \$86 billion semiconductor manufacturing services industry. The company manufactures chips designed for high-growth markets such as mobility, automotive, computing and wired connectivity, consumer internet of things (IoT) and industrial.

As of 2021, GlobalFoundries is the only semiconductor manufacturer with simultaneous operations in Singapore, the European Union, and the United States. The company has one 200mm and one 300mm fabrication plants in Singapore; one 300 mm plant in Dresden, Germany; one 200 mm plant in Burlington, Vermont (where it is the largest private employer)^[6] and two 300 mm plants in New York: one in East Fishkill and one in Malta.^[7]

GlobalFoundries is a "Trusted Foundry" for the U.S. federal government and has similar designations in Singapore and Dresden including certified international Common Criteria standard (ISO 15408, CC Version 3.1).^{[8][9]}

The company has more than 250 customers around the world and has 15,000 employees representing 92 nationalities in 14 countries. GlobalFoundries holds more than 10,000 patents and applications.

CEO Thomas Caulfield has said GlobalFoundries plans to become a publicly traded company in 2022.^[10]

Contents [hide]

200mm & 300mm wafers



GlobalFoundries Inc.



Coordinates: 🥥 37.415293°N 121.974448°W

Туре	Private		
Industry	Semiconductor manufacturer		
Founded	March 2, 2009; 12 years ago		
Headquarters	Malta, New York, U.S.		
Key people	Dr. Thomas Caulfield (CEO) ^[1]		
Products	Semiconductor		
Number of employees	15,000		
Parent	Mubadala Investment Company		
Website	globalfoundries.com 🗹		
Footnotes / references [2]			

Global Foundries



Overview [edit]

On October 7, 2008, AMD announced it planned to go fabless and spin off their semiconductor manufacturing business into a new company temporarily called The Foundry Company. Mubadala announced their subsidiary Advanced Technology Investment Company (ATIC) agreed to pay \$700 million to increase their stake in AMD's semiconductor manufacturing business to 55.6% (up from 8.1%). Mubadala will invest \$314 million for 58 million new shares, increasing their stake in AMD to 19.3%. \$1.2 billion of AMD's debt will be transferred to The Foundry Company.^[11] On 8 December 2008, amendments were announced. AMD will own approximately 34.2% and ATIC will own approximately 65.8% of The Foundry Company.^[12]

On March 4, 2009, GlobalFoundries was officially announced.^[13] On September 7, 2009, ATIC announced it would acquire Chartered Semiconductor for S\$2.5 billion (US\$1.8 billion) and integrate Chartered Semiconductor into GlobalFoundries.^[14] On January 13, 2010, GlobalFoundries announced it had finalized the integration of Chartered Semiconductor.^[15]

On March 4, 2012, AMD announced they divested their final 14% stake in the company, which concluded AMD's multi-year plan to divest its manufacturing arm.^[16]

On October 20, 2014, IBM announced the sale of its microelectronics business to GlobalFoundries.^[17]

As of 2015, the firm owned ten fabrication plants. Fab 1 is in Dresden, Germany. Fabs 2 through 7 are in Singapore. Fabs 8 through 10 are in the northeast United States. These sites are supported by a global network of R&D, design enablement, and customer support in Singapore, China, Taiwan, Japan, India, the United States, Germany, and the United Kingdom.^[18] In February 2017, the company announced a new 300 Fab [Fab 11] in China for growing semiconductor market in China.^[19]

In 2016, GlobalFoundries licensed the 14 nm 14LPP FinFET process from Samsung Electronics. In 2018, GlobalFoundries developed the 12 nm 12LP node based on Samsung's 14 nm 14LPP process.^[20]

On August 27, 2018, GlobalFoundries announced it had cancelled their 7LP process due to a strategy shift to focus on specialized processes instead of leading edge performance.^[21]

On January 29, 2019, AMD announced an amended wafer supply agreement with GlobalFoundries. AMD now has full flexibility for wafer purchases from any foundry at 7 nm or beyond. AMD and GlobalFoundries agreed to commitments and pricing at 12 nm for 2019 through 2021.^[22]

On May 20, 2019, Marvell announced it would acquire Avera Semi from GlobalFoundries for \$650 million and potentially an additional \$90 million. Avera Semi was GlobalFoundries' ASIC Solutions division, which had been a part of IBM's semiconductor manufacturing business.^[23] On February 1, 2019, GlobalFoundries announced the \$236 million sale of its Fab 3E in Tampines, Singapore, to Vanguard International Semiconductor (VIS) as part of their plan to exit the MEMS business by December 31, 2019.^[24] on April 22, 2019, GlobalFoundries announced the \$430 million sale of their Fab 10 in East Fishkill, New York, to ON Semiconductor. GlobalFoundries has received \$100 million and will receive \$330 million at the end of 2022 when ON Semiconductor will gain full operational control. The 300mm fab is capable of 65 nm to 40 nm and was a part of IBM.^[25] On August 15, 2019, GlobalFoundries announced a multi-year supply agreement with Toppan Photomasks. The agreement included Toppan acquiring GlobalFoundries' Burlington photomask facility.^[26]

Process Technology





ASICs

Silicon Photonics

Global Foundries Fabs



Fabrication foundry [edit]

Name	Wafer	Location	Process	
Fab 1	300 mm	Dresden, Germany	Q 51.125°N 13.716°E	55, 45, 40, 32, 28, 22 nm, 12 nm
Fab 2	200 mm	Woodlands, Singapore	Q 1.436°N 103.766°E	600–350 nm
Fab 3/5	200 mm	Woodlands, Singapore	Q 1.436°N 103.766°E	350–180 nm
Fab 3E	200 mm	Tampines, Singapore (2019: sold to VIS)	🔍 1.371°N 103.929°E	180 nm
Fab 6	200 mm	Woodlands, Singapore (converted to 300 mm and merged into Fab 7)	ؼ 1.436°N 103.766°E	180–110 nm
Fab 7	300 mm	Woodlands, Singapore	Q 1.436°N 103.766°E	130–40 nm
Fab 8	300 mm	Luther Forest Technology Campus, Saratoga County, New York, United States	Q 42.970°N 73.756°W	28, 20, 14 nm
Fab 9	200 mm	Essex Junction, Vermont, United States	Q 44.48°N 73.10°W ^[44]	350–90 nm
Fab 10	300 mm	East Fishkill, New York, United States (2019: started transfer to ON Semiconductor)	Q 41.540°N 73.822°W	90–22 nm, 14 nm

DSJ Dr Jeff SO Global Foundries Financials

Seeking Alpha $^{\alpha}$

Symbols, authors, keywords

Q

What's the worst stock in your portfolio? Get Premium to find out »

Written by	Revenue Forecast (\$ mln)	2018	2019	2020	2021	2022F	2023F	2024F
Khaveen	Wafer Shipments 300mm equivalents ('000s) ('a')	1,863	1,758	2,030	2,374	2,586	3,036	3,358
Investments Khaveen Investments is	Growth %		-5.6%	15.5%	16.9%	8.9%	17.4%	11%
a Global Macro Quantamental Hedge Fund managing a	Wafer ASP (Revenue per wafer) ('b')	3,326	3,306	2,389	2,774	3,051	3,034	3,017
portfolio more	Growth %		-0.6%	-27.7%	16.1%	10.0%	-0.6%	-0.6%
Follow	Revenue (\$ mln) ('c')	6,196	5,813	4,851	6,585	7,890	9,212	10,133
4.0K FUIDWEIS	Growth %		-6.2%	-16.6%	35.8%	19.8%	16.7%	10.0%

Foundries





Founded 1987

Chip Shortage





Chip Shortage







TSMC





TSMC



Table 4 – TSMC Customer Share of Revenues 2019-2021					
	2019	2020	2021		
Apple	24.0%	24.2%	25.4%		
Hi-Silicon	15.0%	12.8%	0.0%		
Qualcomm	6.1%	9.8%	7.6%		
NVIDIA	7.6%	7.7%	5.8%		
Broadcom	7.7%	7.6%	8.1%		
AMD	4.0%	7.3%	9.2%		
Intel	5.2%	6.0%	7.2%		
Mediatek	4.3%	5.9%	8.2%		
Source: The Informa	tion Network (www	theinformatio	nnet.com)		

TSMC Process Revenue





1Q21 Revenue by Technology



7nm and Below Revenue

TSMC vs Samsung 5nm



	Samsung ^[24]	TSMC ^[25]
Process name (nm)	5LPE	N5
Transistor density (MTr/mm ²)	127	173 ^[27]
SRAM bit-cell size (µm ²)	0.026	0.017-0.019
Transistor gate pitch (nm)	57	48
Interconnect pitch (nm)	36	28 ^[29]
TSMC vs Samsung 5/7nm



These are real sizes for 7nm node from TS									
			7nm			-			
5	nm		TSMC N7FF ^[71]	Samsung 7LPP ^{[72][73]}	Intel 10 nm	ç			
Samsung ^{[24}] TSMC ^[25]			95.3		ł			
5LPE	N5	Transistor density	96.5 ^[75]	(7LPE) ^[76] 81.07 (57PP)	100.76 ^[78]	1			
127	173 ^[27]	(MTr/mm²)		85.57 (54PP) ^[77]					
0.026	0.017-0.019	SRAM bit-cell size	0.027 µm ^{2[79]}	0.0262 µm ^{2[79]}	0.0312 µm ²	5			
57	48	Transistor Gate Pitch	54 nm	54 nm	54 nm	1 6			
36	28 ^[29]	Transistor Fin Pitch	Unknown	27 nm	34 nm	1 5			
		Transistor Fin Height	Unknown	Unknown	53 nm				
		Minimum (metal) pitch	40 nm	46 nm	36 nm	5			

TSMC's New Fabs in US



TSMC

TSMC Plans Six Wafer Fabs in Arizona

by Scotten Jones on 03-10-2021 at 10:00 am Categories: Foundries, TSMC 7 Comments

Larger than Taiwan?



\$35B

There are reports in the media that TSMC is now planning six Fabs in Arizona (the image above is Fab 18 in Taiwan). The original post I saw referred to a Megafab and claimed six fabs with 100,000 wafers per month of capacity (wpm) for \$35 billion dollars. The report further claimed it would be larger than TSMC fabs in Taiwan.



Now here is a YouTube channel doing the same thing at TSMC's new Phoenix fab.













https://www.youtube.com/watch?v=GU87SH5e0el

https://semiwiki.com/forum/index.php?threads/tsmc-mega-factory-north-phoenix-video-5.15643/

TSMC MEGA Factory North Phoenix Video 5



TSMC on Moore's Law





TSMC Roadmap



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June 2021

TSMC Advanced Technology Roadmap

Production	2015	2016	2017	2018	2019	2020	2021	2022	2023
High-end Premium Mobile Data Center Server Al Accelerator	16FF+	16FFC	N10	N7	N7+	N5	N4	N3	
Mainstream Mid-to-low-end Mobile Networking Consumer	28HPC+	16FFC		12FFC	12FFC+ 16FFC+		NG		N4

TSMC Roadmap



N7+ represents the introduction of EUV lithography to the baseline N7 process. N5 has been in volume production since 2020.

N3 will remain a FinFET-based technology offering, with volume production starting in 2H2022. Compared to N5, N3 will provide:

- +10-15% performance (iso-power)
- -25-30% power (iso-performance)
- +70% logic density
- +20% SRAM density
- +10% analog density



June 2021

TSMC foundation IP has commonly offered two standard cell libraries (of different track heights) to address the unique performance and logic density of the HPC and mobile segments. For N3, the need for "full coverage" of the performance/power (and supply voltage domain) range has led to the introduction of a third standard cell library, as depicted below.

TSMC Roadmap- RF

DR JEFF

US.

June 2021

Dr Jeff

Jeff Drobman ©2016-23

TSMC RF Technology Roadmap



General RF applications: 5G (sub 6 GHz)/4G RF transceiver, WLAN, Bluetooth and etc. mmWave RF applications: 5G mmWave FEM, automotive radar and etc. RF Frontend applications: LNA and switch



TSMC Roadmap: Packaging Jeff Drobman @2016-23

New Plant June 2021

TSMC's planned U.S. plant would involve its latest 3D stacking technologies to arrange chips with different functions in one package, sources told Nikkei Asia.

TSMC is also building an advanced chip packaging facility in the Taiwanese city of Miaoli that is set to go into production in 2022. Advanced Micro Devices and Google will be among the first customers, Nikkei Asia has reported.

The facility would be TSMC's first chip packaging plant outside of Taiwan so this is a very big deal. Chip packaging is an increasingly competitive field but TSMC is on par or even ahead of Intel and Samsung in a short amount of time. The big TSMC advantage is the tight collaboration with big name customers and ecosystem partners.

Per the 2021 TSMC Symposium:

In 2020, TSMC extended their support to encompass 281 distinct process technologies, shipping 11,617 products to 510 customers. As in previous years, TSMC proudly stated "we have never shut down a fab."

Current capacity in 2020 exceeds 12M (12" equivalent) wafers, with expansion investments for both advanced (digital) and specialty process nodes.

TSMC plans to invest a total of US\$100 billion over the next three years, including a US\$30 billion capital expenditure this year, to support global customer needs.

TSMC's global 2020 revenue was \$47.78B – the \$30B annual commit to fab expansion certainly would suggest an expectation of significant and extended semiconductor market growth, especially for the 7nm and 5nm process families. For example, new tapeouts (NTOs) for the 7nm family will be up 60% in 2021.

TSMC has begun construction of a US fab in Phoenix, AZ – volume production of the N5 process will commence in 2024 (~20K wafers per month).



7nm *chiplet*

TSMC + ARM in 3D

ARM quad core A72

Technology 3D Multi-chip Systems

The world's largest foundry joined with partner Arm to announce their new 7nm chiplet system using TSMC's advanced packaging at TSMC's Open Innovation Platform Ecosystem Forum in Santa Clara, Calif., last week.

Rather than the typical SoC with system components arranged on a single die, a chiplet system is optimized for modern HPC processors that partition large multi-core designs into smaller chipsets. This approach allows each chiplet — each die in a package of multiple dice — to be built in different process technologies. The approach is expected to deliver better yields and overall cost-effectiveness.

The TSMC/Arm system is a dual-chiplet implemented in 7nm, with each chiplet containing four Arm Cortex-A72 processors and an on-die interconnect mesh bus. The die-to-die inter-chiplet connection features scalable 0.56pJ/bit (pico-Joules per bit) power efficiency, 1.6Tbps/mm² (terabits per second per square millimeter) bandwidth density, and 0.3V LIPINCON low-voltage interface reaching 8GT/s (giga transactions per second) and 320 Gpbps bandwidth.

"TSMC has the most advanced semiconductor nodes in production, and that gives them some advantages from a silicon side," TechSearch President Jan Vardaman told EE Times. "From a packaging side, each company has an approach that could deliver a similar solution, with TSMC and Intel releasing the most information so far."

TSMC, Arm Show 3DIC Made of Chiplets Source: EE Times (02 Oct 2019)

TSMC New Techs



Abbreviatio	What does it stand for?	What is it?
3DIC	Three-dimensional integrated circuit	
CoWoS	Chip on Wafer on Substrate	TSMC's CoWoS (Chip-on-Wafer-on- Substrate) packaging technology integrates logic and memory chips in a three- dimensional configuration. CoWoS packaged chips are used in artificial intelligence, cloud computing, data center and super computer applications.
InFO	Integrated Fan-Out	TSMC's InFO (Integrated Fan-Out) packaging technology eliminates the substrate used in traditional electronic packages, enabling smaller size, lower power and higher interconnect density.
LIPNCON	Low voltage In Package INterConect	Low-voltage-In-Package-INterCONnect (LIPINCON) is a proprietary system interconnect architecture that facilitates data transmission across all linked components. LIPINCON is an interconnect architecture designed for chiplet designs with advanced packaging technologies such as InFO and CoWoS.
RDL	Redistribution Layer	A redistribution layer (RDL) is an extra metal layer on a chip that makes the IO pads of an integrated circuit available in other locations of the chip, for better access to the pads where necessary.
SolC	Chip 1 Chip 3 Chip 2	SolC is a frontend wafer-process that integrates multi-chip, multi-tier, multi-function and mix-and-match technologies to enable high speed, high bandwidth, low power, high pitch density and minimal footprint and stack-height heterogeneous 3DIC integration

TSMC



TSMC operates four major 300mm manufacturing sites in Taiwan and one in China. The four sites in Taiwan are all GigagFab sites, Fab 12, Fab 14, Fab 15 and Fab 18 are each made up of 6 or 7 wafers fabs sharing central facility plants. This Gigafab approach is believed to reduce construction costs by about 25% versus building a single stand-alone fab. The china fab location is smaller with 2 fabs at one location but the fab was equipped with used equipment transferred from fabs in Taiwan because the fab is trailing edge. If TSMC really builds a single US fab running 20,000 wpm the resulting cost to produce a wafer will be roughly 1.3% higher than for a GigaFab location due to higher construction costs. I believe it is unlikely the site will be equipped with used equipment transferred from Taiwan. The cost to build and equip the fab for 20,000 wpm should be approximately \$5.4 billion dollars.

Locating a fab in the US versus Taiwan will result in the fab incurring US labor and utility costs, this will add approximately 3.4% to the wafer manufacturing cost.

The capacity of the fab is also smaller than a "typical" fab at advanced nodes, the three 5nm fabs TSMC is operating or planning for Taiwan are all 30,000 wpm. A 20,000 wpm fab will have an approximately 3.8% increase in costs versus a 30,000 wpm fab under the same conditions.

In total, wafers produced at the TSMC Arizona fab will be approximately 7% more expensive to manufacturer than a wafer made in Fab 18 in Taiwan. This does not account for the impact of taxes that are likely to be higher in the US than in Taiwan.

In the announcement TSMC has said the total spending on the project between 2021 and 2029 would be \$12 billion dollars. That leaves money for a future expansion or conversion to 3nm. That would be almost enough money to add a second 20,000 wpm fab running 3nm as one possible example.

In summary the "announced" fab would likely be TSMC's highest cost production site. It will be interesting to see if the fab materializes.

Gigafabs

20-30K wpm

\$12B

TSMC in US



Cost Analysis of the Proposed TSMC US Fab

by Scotten Jones on 05-19-2020 at 10:00 am Categories: IC Knowledge, Semiconductor Services, TSMC 29 Comments



On May 15th TSMC "announced its intention to build and operate an advanced semiconductor fab in the United States with the mutual understanding and commitment to support from the U.S. federal government and the State of Arizona."

The fab will run TSMC's 5nm technology and have a capacity of 20,000 wafers per month (wpm). Construction is planned to start in 2021 and production is targeted for 2024. Total spending on the project including capital expenditure will be \$12 billion dollars between 2021 and 2029.

This announcement is undoubtedly the result of intense pressure on TSMC by the US government and it is also coming out today that TSMC will stop taking orders from Huawei also under pressure from the US.

New Chip Fabs

TSMC in Arizona

- THE VERGE



The chip-making industry has production capacity increases planned, but many of the new plants won't be online anytime soon. TSMC and Sony's <u>new \$7 billion chip factory in Japan</u> won't see production start until the end of 2024, the same year as <u>TSMC's new \$12 billion</u> <u>Arizona plant</u>. TSMC has said it plans to invest over \$100 billion in new chip factories over the next three years, while Intel plans to spend a similar amount over the next decade on investments in the US and Europe.

New Chip Fabs

TSMC in Arizona



What is Intel's plan to regain chip market dominance from the likes of TSMC? What are its chances of doing so?



Jeff Drobman, Lecturer at California State University, Northridge (2016present)

Answered just now

-Quora

Apple's mobile A14/15 and MacBook M1 chips are fabbed by TSMC at 5nm. TSMC is the world leader in process density — first to 5nm, with Samsung a close 2nd, and are now testing 3nm. Intel has now joined AMD in using TSMC to fab its high-end chips at 7nm and 5nm. Intel has new plans to catch up, according to this estimate (see slide).

TSMC 4nm



Apple Orders 4nm Chip Production for Next-Generation Macs

Tuesday March 30, 2021 12:35 am PDT by Sami Fathi

Apple has booked the initial production capacity of 4nm chips with long-time supplier TSMC for its next-generation Apple silicon, according to industry sources cited in a new report today from *DigiTimes*.



Apple & TSMC



Apple has already booked the initial capacity of TSMC's N4 for its new-generation Mac series, the sources indicated. Apple has also contracted TSMC to make its nextgeneration <u>iPhone</u> processor dubbed A15, built using the foundry's N5 Plus or N5P process node, the sources said.

TSMC is expected to kick off production for Apple's A15 chip that will power the upcoming iPhone 13 series by the end of May, the sources noted.

The latest Apple silicon, the <u>M1</u> chip, is the first of its kind in the industry based on the 5nm process. The A14 Bionic chip in the <u>iPad Air</u> and <u>iPhone 12</u> lineup is also based on the 5nm process. According to the report, Apple is already looking to the 4nm chip process for its nextgeneration Apple silicon.

A timeframe for when these new 4nm chips will debut isn't provided, but *DigiTimes* does report that TSMC will move to volume production of the new process in Q4 of 2021, ahead of the previously set 2022 timeframe. Additionally, Apple plans to use an enhanced version of the 5nm process for the A15 chip in the iPhone 13, with production set to get underway by the end of May.

The smaller process reduces the chips' actual footprint and provides better efficiency and performance. Apple's expected to launch <u>multiple new Macs</u> this year with more powerful Apple silicon chips; however, there's no indication that any will be based on the 4nm process.

TSMC \$ Apple



Taiwan Semiconductor asked for 2023 price increase from Apple, tech giant said no: report

Sep 28, 2022 11:23 AM ET | **Taiwan Semiconductor Manufacturing Company Limited (TSM)** | Chris Ciaccia, SA News Editor

Taiwan Semiconductor (NYSE:TSM) is slated to raise prices on its customers starting in 2023, but the company's largest customer, Apple (NASDAQ:AAPL), has reportedly told the global foundry no deal.

According to Chinese news outlet Economic Daily News, Taiwan Semiconductor (TSM) wanted to increase the price of the process for its 3 nm process by 3%, which may be used in the A17 chip in some of Apple's (AAPL) Mac computers and perhaps next year's iPhone. However, the tech giant refused and said no, the news outlet said, citing sources. In May, it was reported that Taiwan Semiconductor Manufacturing (TSM) had started to tell some of its customers that it will raise its prices between 5% and 9%, starting next year, due to inflation concerns, rising costs and its expansion.

Cupertino, California-based Apple (AAPL) is Taiwan Semiconductor's (TSM) largest customer and some reports have suggested that it accounts for as much as 25% of the global foundry's annual revenue.

25%

Apple



Bloomberg									US E	US Edition -		
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Technology

Apple Prepares to Get Made-in-US Chips in Pivot From Asia

- Company plans to source chips from Arizona plant in 2024
- CEO Tim Cook makes comments about expansion during meeting

TSMC new fabs in Arizona will open in 2024

TSMC 3nm



SemiWiki.com The Open Forum for Semiconductor Professionals 8-17-22

TSMC's Initial 3nm HVM Yield To Be Better Than Its 5nm

TSMC **N3e** is the HPC version for Intel, AMD, Nvidia, etc... The SoC companies Apple, Mediatek, will use **N3**. Please remember that TSMC sets expectations on the conservative so they don't disappoint. According to my sources N3 for Apple was frozen in December and the N3e process is now frozen with HVM starting in 1H 2023.

> Apple now in production (HVM) with 4nm

Section



TSMC at VLSI Conf 2021



IC Knowledge

VLSI Symposium – TSMC and Imec on Advanced Process and Devices Technology Toward 2nm

by Scotten Jones on 07-02-2021 at 6:00 am Categories: Events, IC Knowledge, Semiconductor Services, TSMC

CMOS Density Improvement

• Logic standard cell area ~ CPP x Cell height





IC Knowledge

VLSI Symposium – TSMC and Imec on Advanced Process and Devices Technology Toward 2nm

by Scotten Jones on 07-02-2021 at 6:00 am

Categories: Events, IC Knowledge, Semiconductor Services, TSMC





IC Knowledge

VLSI Symposium – TSMC and Imec on Advanced Process and Devices Technology Toward 2nm

by Scotten Jones on 07-02-2021 at 6:00 am Categories: Events, IC Knowledge, Semiconductor Services, TSMC

Flexible Sheet Width

· Continuous width adds design flexibility





IC Knowledge

VLSI Symposium – TSMC and Imec on Advanced Process and Devices Technology Toward 2nm by Scotten Jones on 07-02-2021 at 6:00 am

Categories: Events, IC Knowledge, Semiconductor Services, TSMC

Standard Cell height Scaling: Forksheet

• Dielectric wall between N and P: gate isolation, S/D isolation, end cap \downarrow





IC Knowledge

VLSI Symposium – TSMC and Imec on Advanced Process and Devices Technology Toward 2nm

by Scotten Jones on 07-02-2021 at 6:00 am Categories: Events, IC Knowledge, Semiconductor Services, TSMC





IC Knowledge

VLSI Symposium – TSMC and Imec on Advanced Process and Devices Technology Toward 2nm

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IC Knowledge

VLSI Symposium – TSMC and Imec on Advanced Process and Devices Technology Toward 2nm

by Scotten Jones on 07-02-2021 at 6:00 am

Categories: Events, IC Knowledge, Semiconductor Services, TSMC





IC Knowledge

VLSI Symposium – TSMC and Imec on Advanced Process and Devices Technology Toward 2nm

by Scotten Jones on 07-02-2021 at 6:00 am

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Figure 10. HNS Process Flow.



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Forksheet process flow

Light Blue: New modules in FS Blue: Modified modules from NS

- Nanosheet STI
- **Dielectric wall formation**

Gate patterning

- Spacer and fin recess
- Inner spacer
- Source/drain epitaxy
- ILD0 CMP
- Dummy poly/oxide removal
- NS channel release by SiGe etch

RMG

MOL + BEOL

Forksheet flow is similar as nanosheet flow. Dielectric wall formation and modified inner spacer/SD epi/RMG are key process steps.

See more details in H. Mertens et al. VLSI2021 T2-1



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TSMC Slides



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TSMC Slides



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Figure 15. CFET Fabrication Options.

Section



TSMC at VLSI Conf 2022





DR JEFF

Dr Jef

Jeff Drobman ©2016-23



TSMC has merged their 2.5D and 3D packaging offerings into a single brand – "3D Fabric". The expectations are that there will be future customers that pursue both options to provide dense, heterogeneous integration of system-level functionality – e.g., both "front-end" 3D vertical assembly, combined with "back-end" 2.5D integration.



<u>N5/N4</u>

- in the 3rd year of production, with over 2M wafers shipped, 150 NTOs by yearend 2022
- mobile customers were the first, followed by HPC products
- roadmap includes ongoing N4 process enhancements
- N4P foundation IP is ready, interface IP available in 3Q2022 (to the v1.0 PDK)
- there is an N5HPC variant (not shown in the figure above, ~8% perf improvement, HVM in 2H22)

Node (compared to N5)	N5	N5P	N4P	N4X
Performance	1X	1.05X	1.11X	1.15X
Density	1X	1X	1.06X	1.06X







As shown below, InFO_PoP denotes a package-on-package configuration, and is focused on integration of a DRAM package with a base logic die. The bumps on the DRAM top die utilize through-InFO vias (TIV) to reach the redistribution layers.



Foundries





Founded 1938

Intel vs Samsung



FOUNDRIES

How Intel will Beat Samsung by Daniel Nenni on 03-09-2022 at 6:00 am Categories: Foundries 7 Comments



Now that Intel is back in the foundry business, and with the Tower Semiconductor acquisition they are definitely back in the foundry business, Samsung will be the biggest foundry loser here.

You can break the IDM foundry business into two parts: First, and foremost, the NOT TSMC Business. Second is the the Better PPA (Power/Performance, Area) Business.



Samsung 12" Wafers



Chip Fabs



-**THE VERGE** Samsung in Texas Samsung in Texas Samsung is building a new \$17 billion advanced chip plant in Texas

Creating 1,800 jobs in the city of Taylor

By Mitchell Clark and Jon Porter | Updated Nov 23, 2021, 6:15pm EST



Samsung Austin Semiconductor — The new plant will be even larger than this | Image: Samsung

Chip Fabs



Kinam Kim, the vice chairman and CEO of Samsung Electronics Device Solutions Division says in a statement that "With greater manufacturing capacity, we will be able to better serve the needs of our customers and contribute to the stability of the global semiconductor supply chain." He continued, "In addition to our partners in Texas, we are grateful to the Biden Administration for creating an environment that supports companies like Samsung as we work to expand leading-edge semiconductor manufacturing in the U.S. We also thank the administration and Congress for their bipartisan support to swiftly enact federal incentives for domestic chip production and innovation."

In response, the Biden administration is attempting to bolster US chip production, reducing the potential for supply chain disruption and reversing the country's declining share of manufacturing in recent decades. The Senate recently approved \$52 billion in subsidies for new chipmaking plants, though the CHIPS Act is yet to pass in the House of Representatives, according to *Bloomberg*.

Samsung 3nm



July 2021

Samsung 3nm GAA HVM in 2024?

Samsung Foundry 3nm Gate All Around Process Node, 3GAE, Delayed to 2024

Samsung Foundry 3nm Gate All Around Process Node, 3GAE, Delayed to 2024! This would arrive in a similar time frame to TSMC's denser 2nm GAA technology.Samsung and Intel continue to slip further behind TSMC in leading edge technology. Will they ever be able to catch up?

Samsung Processes





Figure 1. Logic Roadmap.

n figure 1 we can see how the contacted poly pitch (CPP) of logic processes has caled over time. In the planar era we saw high-k metal gate (HKMG) introduced by ntel at 45nm and by the foundries at 28nm as well as innovations like embedded

Samsung DRAM Processes





Figure 2 DRAM Roadmap

With EUV already ramping up in DRAM, the next challenges are shrinking the memory cell. Samsung is anticipating staking two layers of capacitors soon. A switch

Samsung NAND Processes



IC Knowledge



Samsung Keynote at IEDM

by Scotten Jones on 01-27-2022 at 6:00 am



Figure 3 NAND Roadmap

Samsung's latest 3D NAND is a 176-layer process that uses string stacking for the first time (first time string stacking for them, others have been string stacking for multiple generations) and peripheral under the array for the first time (once again the



SemiWiki.com

Via Apple

Fabless: The Transformation of the Semiconductor Industry

Samsung entered the foundry business with Apple 15+ years ago. The first Apple ASIC (iPod) was actually done by fabless ASIC vendor eSilicon and the volumes were drastically underestimated so eSilicon profited greatly. In 2006 Steve Jobs went to Intel CEO Paul Otellini and pitched the iPhone in hopes of getting a manufacturing agreement. Paul did not share Steve's vision and passed on the deal:

"We ended up not winning it or passing on it, depending on how you want to view it. And the world would have been a lot different if we'd done it. The thing you have to remember is that this was before the iPhone was introduced and no one knew what the iPhone would do. At the end of the day, there was a chip that they were interested in that they wanted to pay a certain price for and not a nickel more and that price was below our forecasted cost. I couldn't see it. It wasn't one of these things you can make up on volume. And in hindsight, the forecasted cost was wrong and the volume was 100x what anyone thought."

As a result, not only did Intel miss the mobile market, they missed the opportunity of being a world class foundry like TSMC is today.



SemiWiki.com

Via Apple

Apple then went to Samsung which produced the first A4 SoC for the iPhone 4 using the Samsung 45nm process. The A5 SoC was also 45nm. Back then we named processes different so it was not unusual to reuse a process so all was well and the iPhone dynasty had begun. The A6 was Samsung 32nm and the A7 was Samsung 28nm.

Unfortunately, Samsung showed their true IDM colors by competing directly with Apple and even borrowed some Apple IP. The result was Apple filing more than 50 legal actions around the world which would ultimately be settled for billions of dollars in Apple's favor.

For the A8 (iPhone 6) Apple turned to TSMC 20nm. The iPhone 6 was one of the better smartphones (I had one). Unfortunately, when Apple turned to FinFETs TSMC could not supply enough chips so they also used Samsung 14nm for the A9. Apple was back to TSMC for the A9x and there on after.



SemiWiki.com

Via Apple

Apple absolutely did change the foundry business by writing some really big checks, accounting for 20+% of TSMCs annual revenue, but also for the yearly process cadence. Rather than taking big risky steps TSMC did yearly half nodes matched with the yearly fall iProducts launch. This allowed them to perfect double patterning before adding FinFETs, introduce partial EUV before going to full EUV, and many other process innovations. It's called yield learning for a reason.

Now Samsung and Intel both follow the half node process methodology and you can thank Apple for that, absolutely.

Which brings us back to the recent Samsung missteps. Samsung did VERY well at 14nm getting a piece of the Apple business and many other customers including Qualcomm. Globalfoundries also licensed Samsung 14nm for their Malta fab and has done quite well with it so Samsung 14nm customers are far reaching. Unfortunately, 10nm was not so kind to Samsung with single digit yields at launch time. Samsung was forced to ship good die instead of wafers causing Qualcomm and others to miss market windows and customer commitments.





Via Apple

Samsung did a much better job at 7nm but now we are hearing about a serious unreported yield problem at 5nm. In fact, there is a formal investigation inside Samsung:

"The company's management suspects a forgery of the report on the release of microcircuits by the Samsung Semiconductor Foundry division. Information about the production of 5-, 4- and 3-nm products is now being verified..."

Foundries





Founded 1911

IBM \$20B



10-6-22









Images of IBMs 2nm Chip architecture

New Processes





2-3-5-7 nm Comps



Peak Quoted Transistor Densities (MTr/mm2)

AnandTech	IBM	TSMC	Intel	Samsung
22nm			16.50	
16nm/14nm		28.88	44.67	33.32
10nm		52.51	100.76	51.82
7nm		91.20	237.18*	95.08
5nm		171.30		
3nm		292.21*		
2nm	333.33			

Data from Wikichip, Different Fabs may have different counting methodologies * Estimated Logic Density

Wikichip

Chips





Process Nodes in China



SIA SEMICONDUCTOR INDUSTRY ASSOCIATION





Source: SIA Research





SIA SEMICONDUCTOR INDUSTRY ASSOCIATION

Chinese Share in the Global Semiconductor Supply Chain by Major Segment



Source: BCG x SIA: Strengthening the Global Semiconductor Supply Chain in an Uncertain Era

China Map



S I A SEMICONDUCTOR INDUSTRY ASSOCIATION	SMIC	
New Fab Projects in 2021		Qingdao HKC Phase II 12" Discrete Fat Sai Micro 6/8" GaN-on-Si Fab, \$0.2bn
		Yangjie 8'' Auto Chip Fab, \$0.1bn Guangxin 6'' Power Device Fab, \$0.1br
Yandong Micro 12" Analog Fab, \$0.7bn Anxin Semi 6/8" Power Fab, \$0.1bn Rongxin Semi 12" Analog Fab, \$0.3bn		SMIC Shanghai12" JV Fab, \$8.9bn WeEn Shanghai Analog Fab, \$0.1bn Xinwu 12" Sensor Fab, \$0.3bn
HiWafer Phase II GaN Fab, \$1.6bn Mianyang Gov't 8" Fab, \$1.3bn		SMIC Shaoxing 6/8" SiC Fab, \$2.5bn
Aosong 8" MEMS Fab, \$0.5bn Guangdong 6" SiC Pilot Fab, \$0.1bn Bronze Technology SiC Fab, \$0.1bn	La contraction of the second s	Huntersun 8" MEMS Fab, \$0.3bn Rongwang Semi 8" Discrete Fab Yiwu Gov't 8" fab
Yitoa Intelligent 6" SiC Fab		Fuzhou Gov't 8" GaN Fab, \$1bn

Top China Chip Firms

DR JEFF

DS.

Dr Jeff

Jeff Drobman ©2016-23



Source: SIA analysis

China OEM's



S I A SEMICONDUCTOR INDUSTRY ASSOCIATION

Chinese OEMs and Their Commercially Available Chip Products

OEM Vertical	Company	Semiconductor Efforts		
- Consumer Electronics	nı	 Jun. 2021, recruiting new chip design team As of Aug. 2021, Xiaomi's VC fund invested in over 60 semiconductor companies 		
	cetete	Feb 2020, unveiled "Mariana" chip development plan		
	vivo	 Aug. 2021, invested in power semiconductor company 		
	huami	Jul. 2021, launched dual-core RISC-V wearable device processor		
		 Feb. 2020, developed samples of GaN-based MicroLED chip May. 2020, started memory ATP project 		
- Home Appliances -	Galanz	 Jan. 2021, testing RISC-V home appliance chips in foreign markets 		
	Midea	Jan. 2021, incorporated semiconductor subsidiaries		
	TCL	Mar. 2021, incorporated two semiconductor subsidiaries		
	CHANGHONG EE SI	 Aug. 2020, teams up with HiSilicon on 5G chip development 		
	Alibaba Group 海軍世営用目	 May 2021, launched Xuantie 907 RISC-V processor Oct. 2021, unveiled 5nm Yitian 710 		
Internet Cloud Service	Bai de 百度	 Jun. 2021, incorporated chip subsidiary Aug. 2021, 2nd generation XPU 		
	hu 字节跳动	Mar. 2021, developing AI and server chips in-house		
	Tencent	Jul. 2021, developing special purpose processors in-house		
	🗯 Meituan	 Jul. 2021, set up chip subsidiaries Aug. 2021, invested in chip IDM 		
Telecom and Network	st huawei	As of Aug. 2021, Hubble Technology invested in 44 companies in semiconductor supply chain		
Equipment	HBC	 Oct. 2020, launched first switch chip Apr. 2021, launched first network processor 		

Source: SIA analysis

China Chip Designers





Source: SIA analysis

Foundries



Wafer Scale

Wafer Scale



2019

Cerebras Wafer Scale Integration



The Cerebras device packs 84 tiles in a 7x12 array. Each includes about 4,800 cores geared for AI's sparse linear algebra with 48 KBytes SRAM each.

Cerebras WSE 2 Wafer Scale Engine





...

--Cerebras Systems Cerebras Wafer Scale Engine 2

Shift to 7-nanometer process boosts the second-generation chip's transistor count to a mind boggling 2.6-trillion

Almost from the moment Cerebras Systems announced a computer based on the largest single computer chip ever built, the Silicon Valley startup declared its intentions to build an even heftier processor. Today, the company announced that its next-gen chip, the Wafer Scale Engine 2 (WSE 2), will be available in the 3rd quarter of this year. WSE 2 is just as big physically as its predecessor, but it has enormously increased amounts of, well, everything.

As big as possible, meaning the size of an entire wafer of silicon (with the round bits cut off), or 46,225 square millimeters.

	WSE 2	WSE	Nvidia A100
Size	46,255 mm ²	46,255 mm ²	826 mm ²
Transistors	2.6 trillion	1.2 trillion	54.2 billion
Cores	850,000	400,000	7,344
On-chip memory	40 gigabytes	18 GB	40 megabytes
Memory bandwidth	20 petabytes/s	9 PB/s	155 GB/s
Fabric bandwidth	220 petabits/s	100 Pb/s	600 gigabytes/s
Fabrication process	7 nm	16 nm	7 nm

UCLA Wafer Scale



UCLA Sa

Samueli School of Engineering

ABOUT NEWS & EVENTS RESEARCH & ACADEMICS ADMISSIONS SU

At Cal State Los Angeles, physiology and neuroscience researcher Selvan Joseph is one such innovator. He's using the Flextrate platform developed at CHIPS to design sensors that can track the physical movements and muscle activity of patients with movement disorders, or those recovering from spinal cord injuries. Flextrate allows him to put these sensors in a small flexible patch that patients can wear unobtrusively on their skin.

Flextrate

Chiplets?

"This technology is definitely a game-changer in that you can create devices with more flexibility, pliability and portability," Joseph said. "We can send this device home with our patients and then remote collect data in real time in their day-to-day lives."





While these platforms have the potential to revolutionize data centers, and consumer and medical electronics, the CHIPS team is also working on ways to make supercomputers and artificial intelligence machines more powerful in the wake of Moore's Law.